

Power Matters.™

Home ▶ 2N5630 (#23408)

Products

- ▶ Product Directory
- ▶ Applications Directory
- ▶ Parametric Search

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Overview

Diagrams

Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector to Emitter Saturation Voltage	V _{CE(sat)}			1.00	V
DC Current Gain	HFE	20.00		80.00	

Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	V _{BR(CBO)}			120.00	V
Collector Current (dc)	I _C			16.00	A
Collector-Emitter Voltage (Base Open)	V _{CEO}			120.00	V
Emitter-Base Voltage (Collector Open)	V _{EBO}			7.00	V
Power Dissipation, Total	P _T			200.00	W

This part can be found in the following product categories:

- ▶ Discretes ▶ Transistors ▶ BJT(BiPolar Junction Transistor) ▶ **FNP** Transistor
- ▶ Non-Radiation Hardened Devices ▶ Transistors ▶ BJT(BiPolar Junction Transistor) ▶ **NPN** Transistor

Related Links

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